

2SC5080

Silicon NPN Epitaxial

REJ03G0742-0300
 (Previous ADE-208-1132A)
 Rev.3.00
 Aug.10.2005

Application

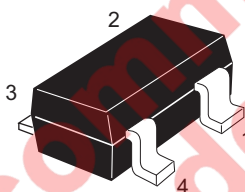
VHF / UHF wide band amplifier

Features

- High gain bandwidth product
 $f_T = 13.5$ GHz Typ
- High gain, low noise figure
 $PG = 18$ dB Typ, $NF = 1.1$ dB Typ at $f = 900$ MHz

Outline

RENESAS Package code: PLSP0004ZA-A
 (Package name: MPAK-4)



1. Collector
2. Emitter
3. Base
4. Emitter

Note: Marking is "ZD-".

Attention: This device is very sensitive to electro static discharge.

It is recommended to adopt appropriate cautions when handling this transistor.

Absolute Maximum Ratings

($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	15	V
Collector to emitter voltage	V_{CEO}	8	V
Emitter to base voltage	V_{EBO}	1.5	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

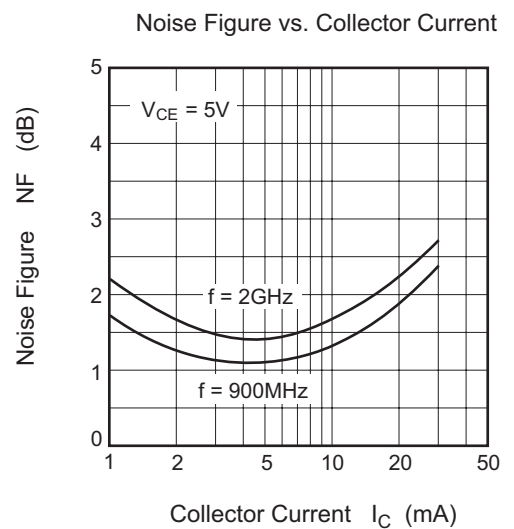
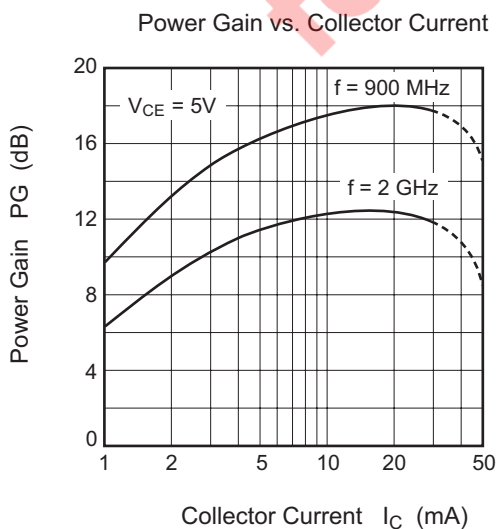
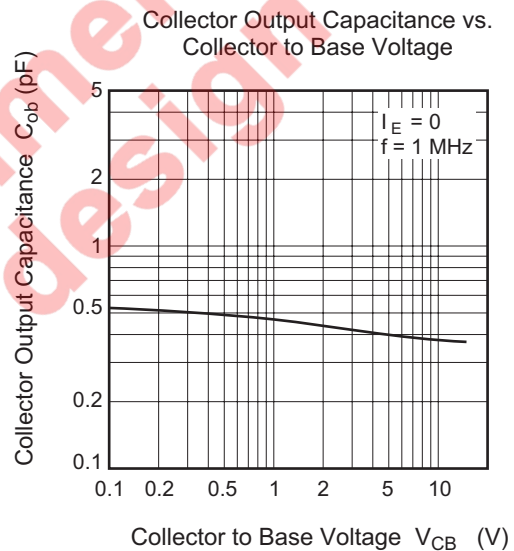
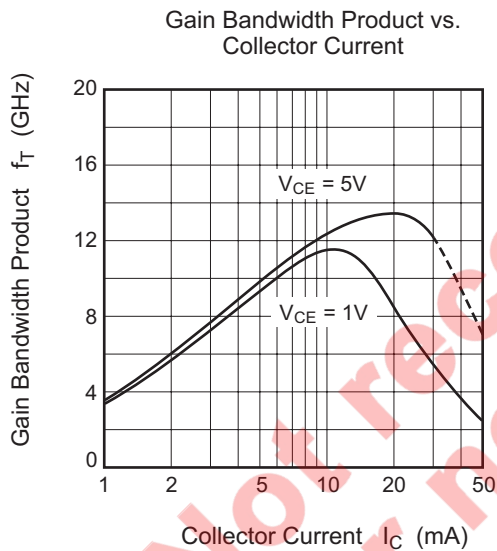
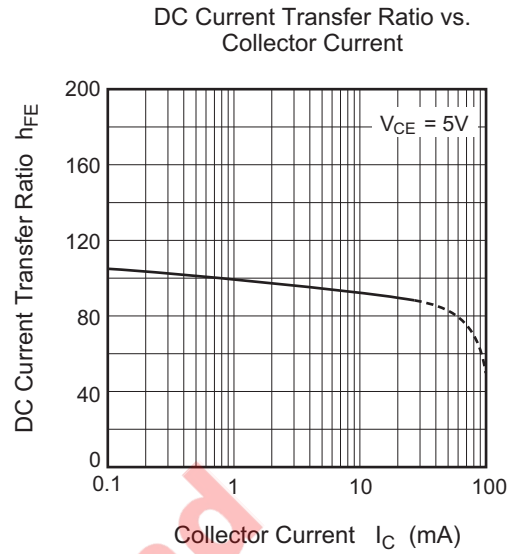
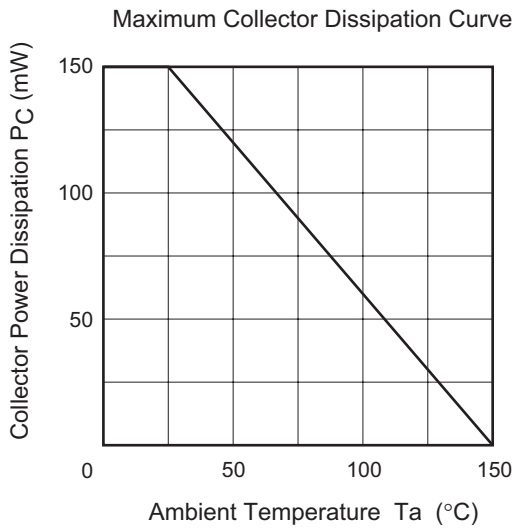
Electrical Characteristics

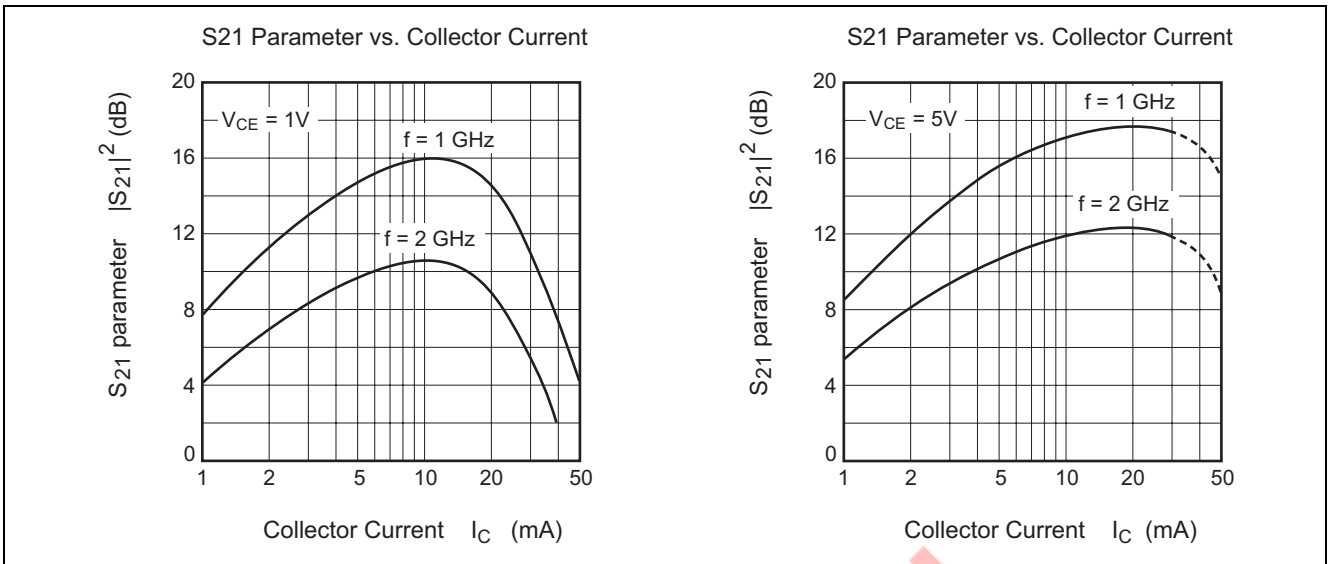
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	15	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector cutoff current	I_{CBO}	—	—	1	μA	$V_{CB} = 12 V, I_E = 0$
	I_{CEO}	—	—	1	mA	$V_{CE} = 8 V, R_{BE} = \infty$
Emitter cutoff current	I_{EBO}	—	—	10	μA	$V_{EB} = 1.5 V, I_C = 0$
DC current transfer ratio	h_{FE}	50	90	160		$V_{CE} = 5 V, I_C = 20 mA$
Collector output capacitance	C_{ob}	—	0.4	0.75	pF	$V_{CB} = 5 V, I_E = 0, f = 1 MHz$
Gain bandwidth product	f_T	10.5	13.5	—	GHz	$V_{CE} = 5 V, I_C = 20 mA$
Power gain	PG	15	18	—	dB	$V_{CE} = 5 V, I_C = 20 mA,$ $f = 900 MHz$
Noise figure	NF	—	1.1	2.0	dB	$V_{CE} = 5 V, I_C = 5 mA,$ $f = 900 MHz$

Not recommend
for new design

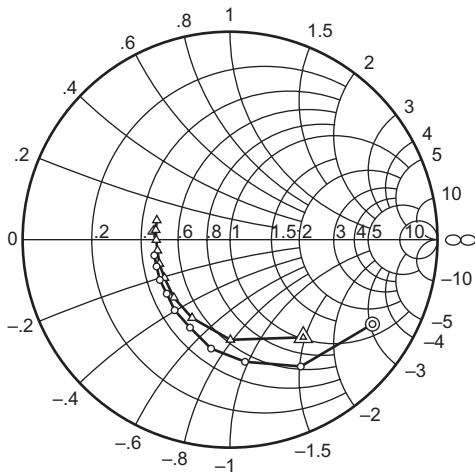
Main Characteristics





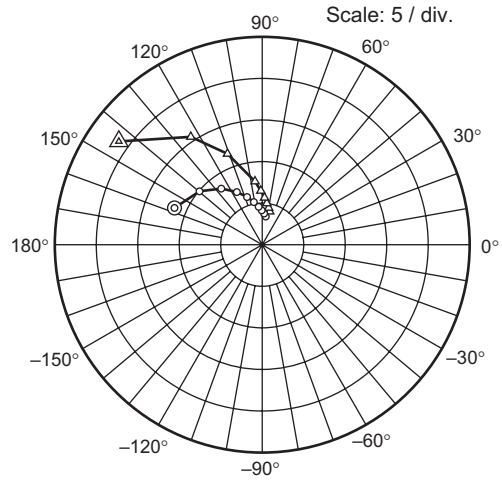
Not recommended
for new design

S11 Parameter vs. Frequency



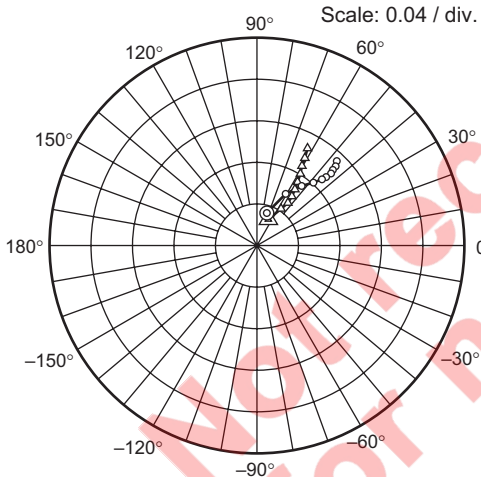
Condition: $V_{CE} = 5\text{ V}$, $Z_o = 50\ \Omega$
 200 to 2000 MHz (200 MHz step)
 ○ — ○ ($I_C = 5\text{ mA}$)
 △ — △ ($I_C = 20\text{ mA}$)

S21 Parameter vs. Frequency



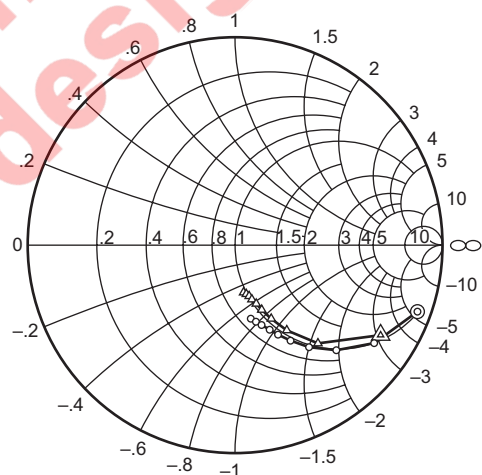
Condition: $V_{CE} = 5\text{ V}$, $Z_o = 50\ \Omega$
 200 to 2000 MHz (200 MHz step)
 ○ — ○ ($I_C = 5\text{ mA}$)
 △ — △ ($I_C = 20\text{ mA}$)

S12 Parameter vs. Frequency



Condition: $V_{CE} = 5\text{ V}$, $Z_o = 50\ \Omega$
 200 to 2000 MHz (200 MHz step)
 ○ — ○ ($I_C = 5\text{ mA}$)
 △ — △ ($I_C = 20\text{ mA}$)

S22 Parameter vs. Frequency



Condition: $V_{CE} = 5\text{ V}$, $Z_o = 50\ \Omega$
 200 to 2000 MHz (200 MHz step)
 ○ — ○ ($I_C = 5\text{ mA}$)
 △ — △ ($I_C = 20\text{ mA}$)

S Parameters

 $(V_{CE} = 5 \text{ V}, I_C = 5 \text{ mA}, Z_O = 50 \Omega)$

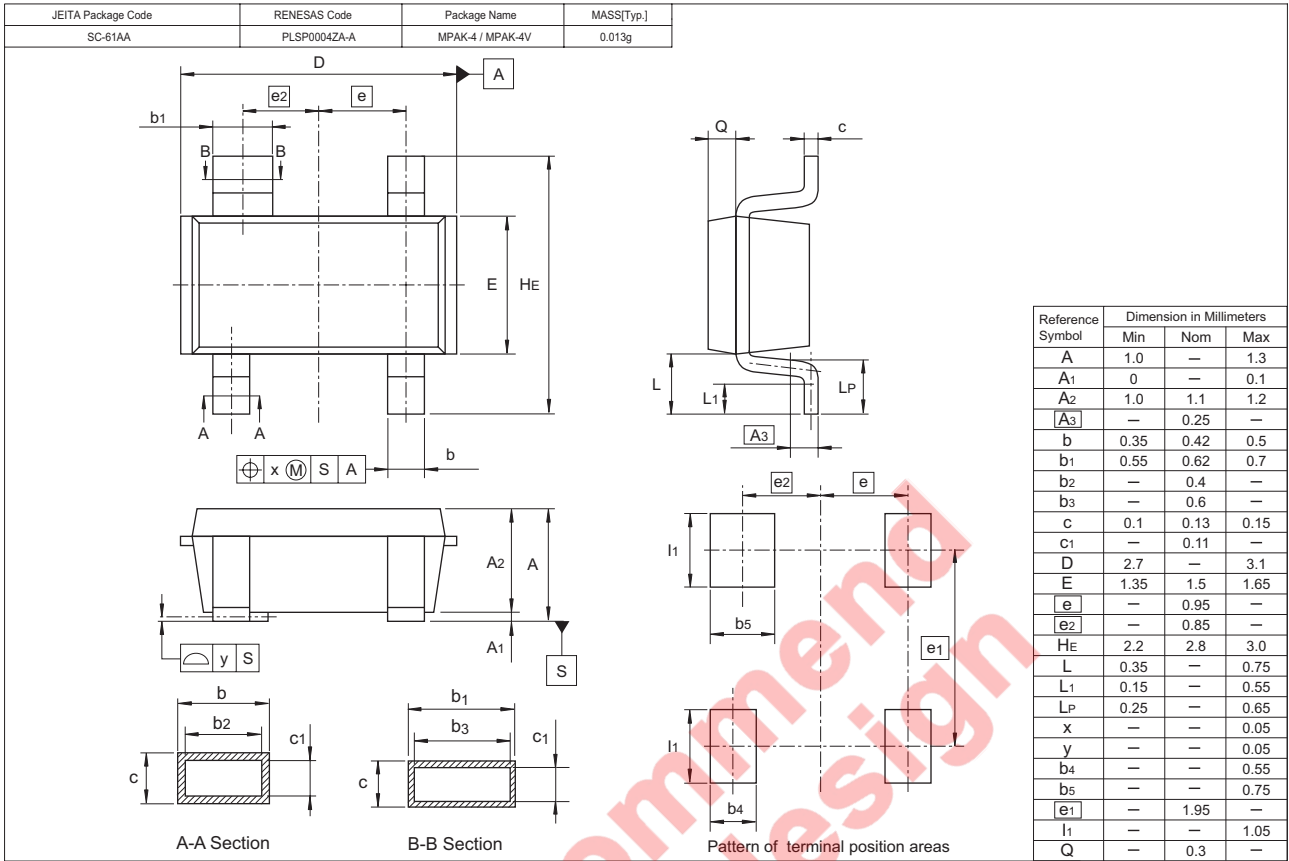
Freq. (MHz)	S11		S21		S12		S22	
	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
200	0.798	-30.8	11.47	157.3	0.0329	73.0	0.936	-20.0
400	0.699	-60.8	9.88	139.6	0.0570	60.8	0.820	-35.1
600	0.592	-83.0	8.35	126.1	0.0718	53.0	0.703	-46.0
800	0.532	-99.9	7.03	115.7	0.0817	48.0	0.607	-54.0
1000	0.465	-114.5	6.02	107.6	0.0891	45.4	0.532	-59.8
1200	0.432	-128.2	5.23	101.0	0.0939	44.6	0.478	-64.3
1400	0.401	-139.6	4.58	95.2	0.0993	44.1	0.440	-67.7
1600	0.390	-150.2	4.14	90.7	0.103	44.8	0.405	-71.6
1800	0.373	-160.5	3.76	86.4	0.108	45.1	0.382	-74.7
2000	0.373	-168.3	3.42	82.6	0.112	46.5	0.362	-77.9

S Parameters

 $(V_{CE} = 5 \text{ V}, I_C = 20 \text{ mA}, Z_O = 50 \Omega)$

Freq. (MHz)	S11		S21		S12		S22	
	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
200	0.588	-53.1	21.24	144.3	0.0275	66.3	0.826	-31.8
400	0.482	-89.8	15.59	123.6	0.0423	56.6	0.619	-49.8
600	0.419	-115.9	11.75	111.0	0.0507	53.9	0.480	-58.7
800	0.389	-134.1	9.29	102.4	0.0581	54.5	0.395	-63.8
1000	0.366	-149.7	7.64	96.5	0.0652	55.8	0.337	-67.6
1200	0.365	-161.9	6.47	91.4	0.0726	57.3	0.300	-70.1
1400	0.354	-171.4	5.63	97.1	0.0806	58.7	0.274	-72.8
1600	0.356	-179.7	4.98	83.5	0.0877	60.4	0.255	-74.6
1800	0.361	172.7	4.48	79.9	0.0959	61.2	0.242	-77.1
2000	0.365	165.3	4.06	77.0	0.105	62.4	0.232	-79.9

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SC5080ZD-TL-E	3000	φ 178 mm Reel, 8 mm Emboss Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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